

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
-65V	8Ω @ V _{GS} = -5V	-318mA
	18Ω @ V _{GS} = -2.5V	-212mA

Features and Benefits

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please [contact us](mailto:contact@diodes.com) or your local Diodes representative. <https://www.diodes.com/quality/product-definitions/>**

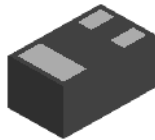
Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

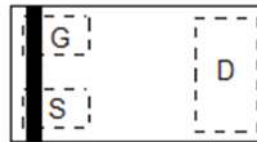
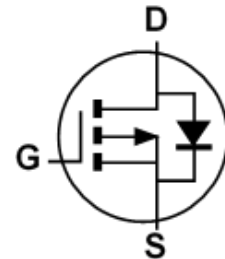
- DC-DC Converters
- Power Management Functions
- Battery Operated Systems and Solid-State Relays
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.

Mechanical Data

- Case: X1-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu. Solderable per MIL-STD-202, Method 208 (e4)
- Weight: 0.001 grams (Approximate)

X1-DFN1006-3


Bottom View


 Top View
Pin-Out


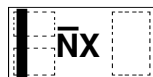
Equivalent Circuit

Ordering Information (Note 4)

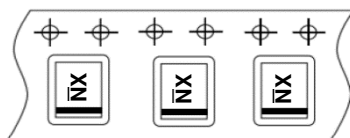
Part Number	Case	Packaging
DMP68D0LFB-7B	X1-DFN1006-3	10,000 / Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information

X1-DFN1006-3

 Top View
Bar Denotes Gate and Source Side

NX = Part Marking Code



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-65	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 5) V _{GS} = -5V	Steady State	T _A = +25°C	I _D	-192	mA
		T _A = +70°C		-153	
Continuous Drain Current (Note 6) V _{GS} = -5V	Steady State	T _A = +25°C	I _D	-318	mA
		T _A = +70°C		-254	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	-800	mA
Maximum Body Diode Continuous Current (Note 6)			I _S	-318	mA

Thermal Characteristics

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 5)	P _D	0.5	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	R _{θJA}	251	°C/W
Power Dissipation (Note 6)	P _D	1.21	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 6)	R _{θJA}	103	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-65	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1.0	µA	V _{DS} = -65V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(TH)}	-0.8	—	-2.1	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	2.0	8	Ω	V _{GS} = -5V, I _D = -100mA
		—	4.7	18	Ω	V _{GS} = -2.5V, I _D = -10mA
Diode Forward Voltage	V _{SD}	—	-0.8	-1.5	V	V _{GS} = 0V, I _S = -100mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	36	—	pF	V _{DS} = -30V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	3.9	—		
Reverse Transfer Capacitance	C _{rss}	—	2.1	—		
Gate Resistance	R _g	—	247	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	—	4.1	—	nC	V _{GS} = -5V, V _{DS} = -30V, I _D = -100mA
Gate-Source Charge	Q _{gs}	—	1.3	—		
Gate-Drain Charge	Q _{gd}	—	1.3	—		
Turn-On Delay Time	t _{D(ON)}	—	12.2	—	ns	V _{GS} = -5V, V _{DS} = -30V, R _G = 50Ω, I _D = -100mA
Turn-On Rise Time	t _R	—	10.6	—		
Turn-Off Delay Time	t _{D(OFF)}	—	33.2	—		
Turn-Off Fall Time	t _F	—	18.9	—		

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

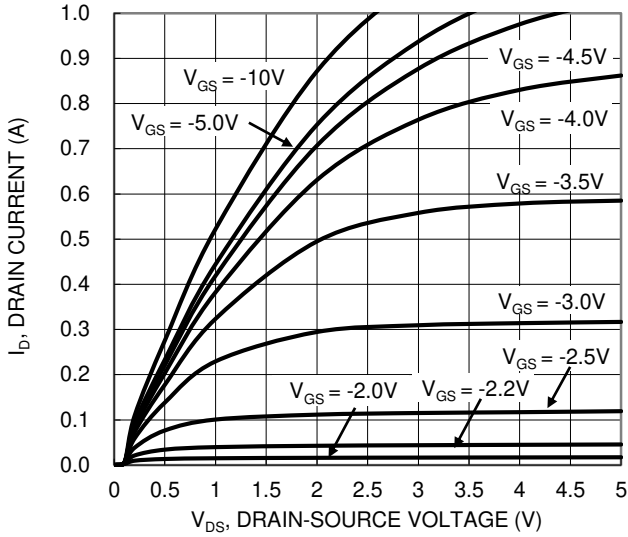


Figure 1. Typical Output Characteristic

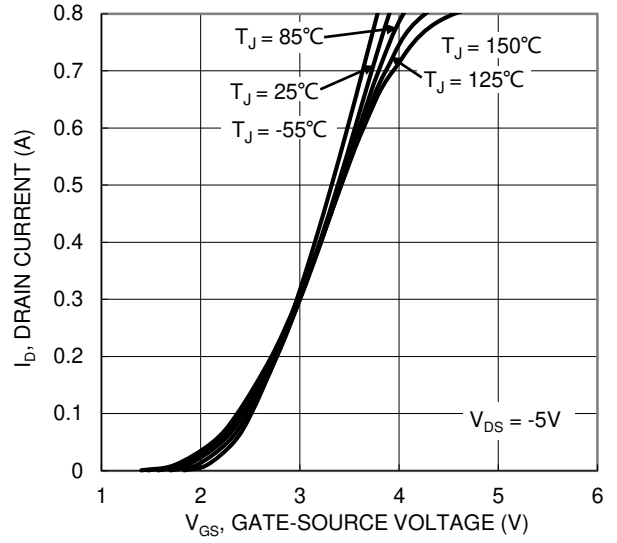


Figure 2. Typical Transfer Characteristic

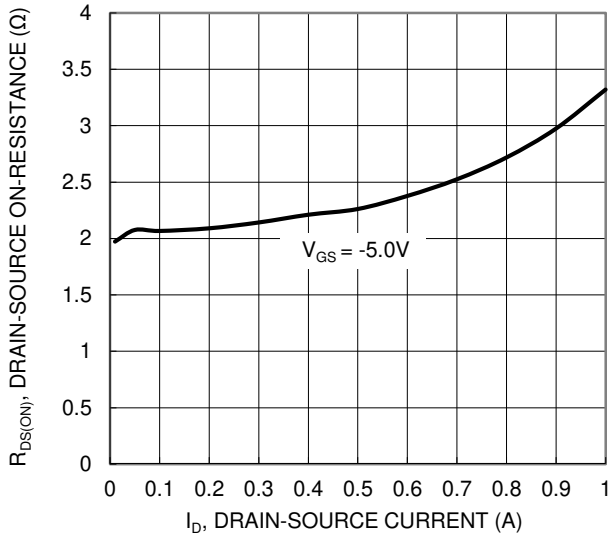


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

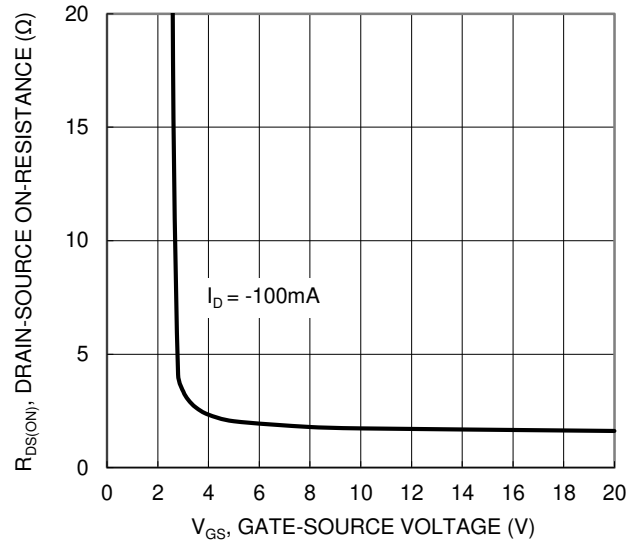


Figure 4. Typical Transfer Characteristic

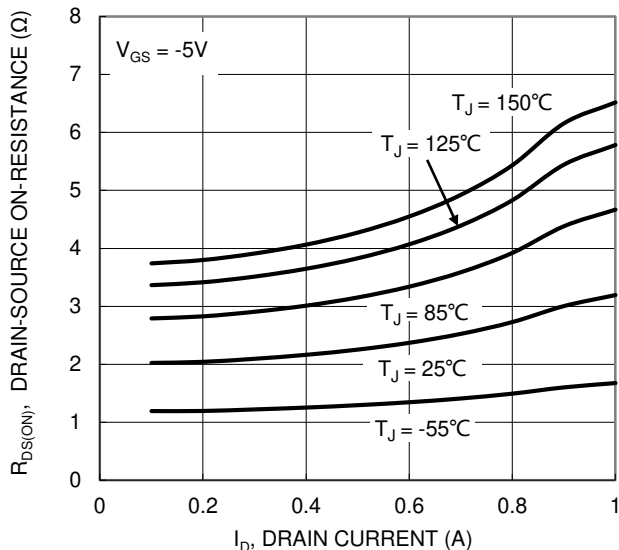


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

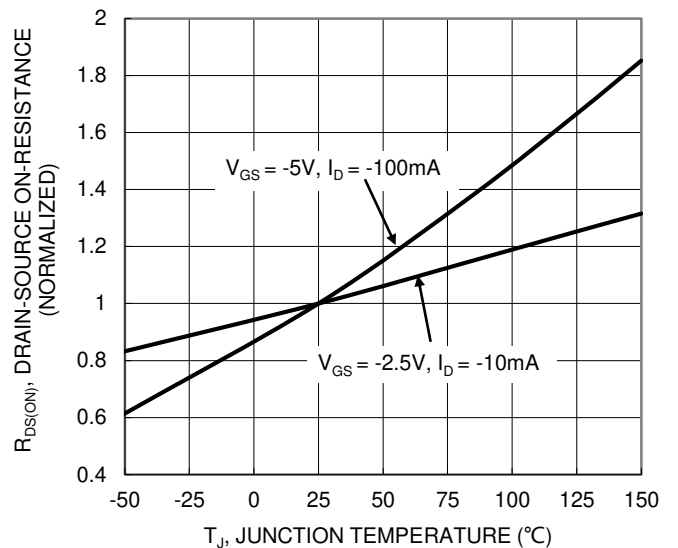


Figure 6. On-Resistance Variation with Junction Temperature

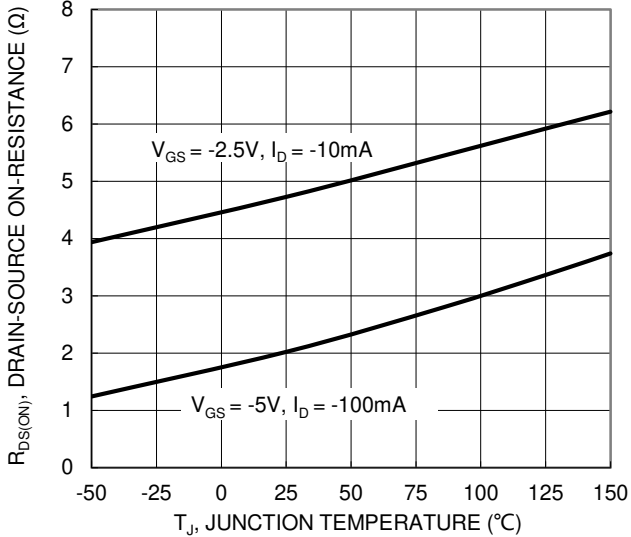


Figure 7. On-Resistance Variation with Junction Temperature

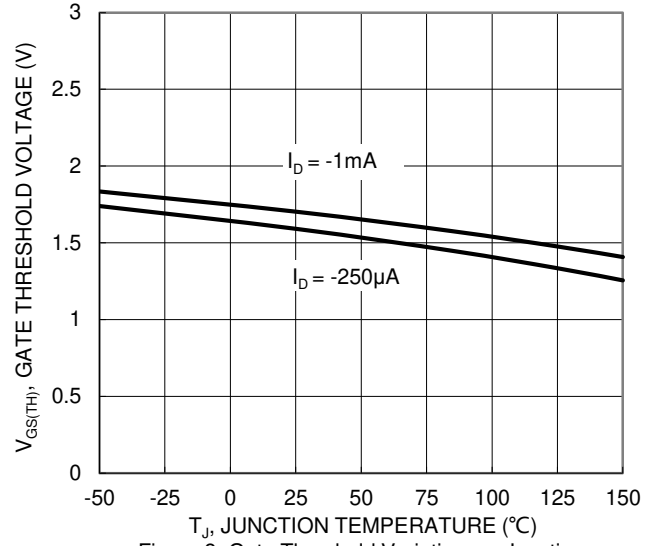


Figure 8. Gate Threshold Variation vs. Junction Temperature

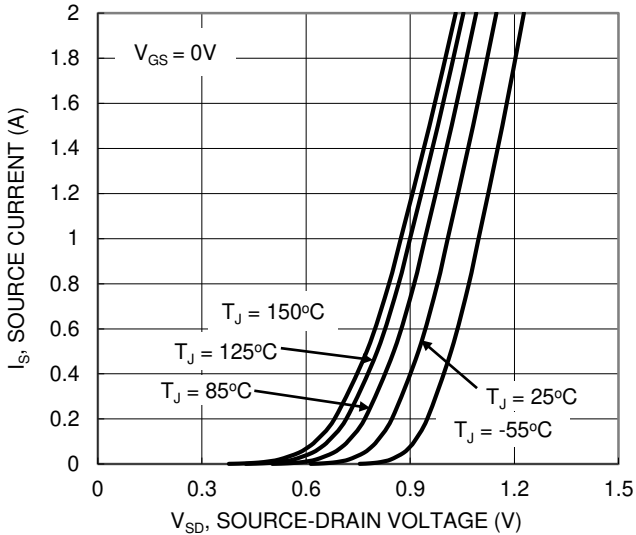


Figure 9. Diode Forward Voltage vs. Current

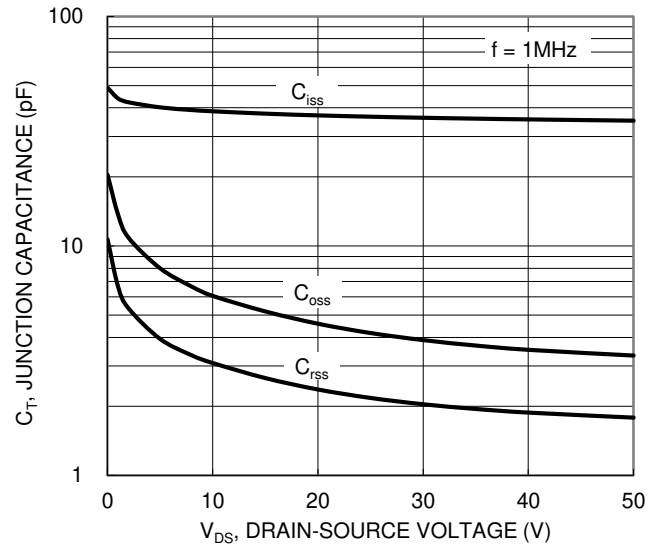


Figure 10. Typical Junction Capacitance

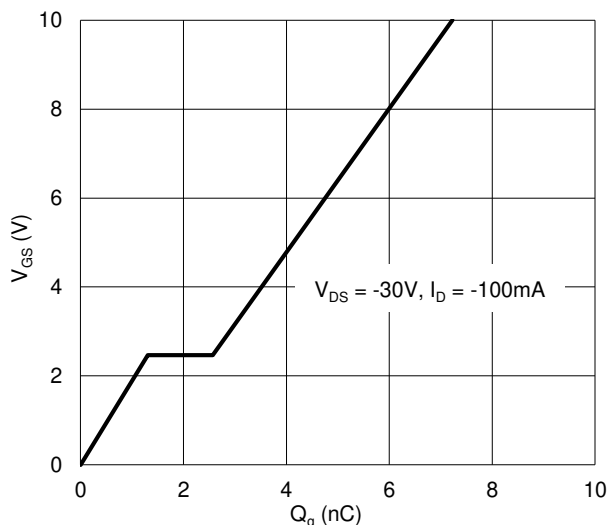


Figure 11. Gate Charge

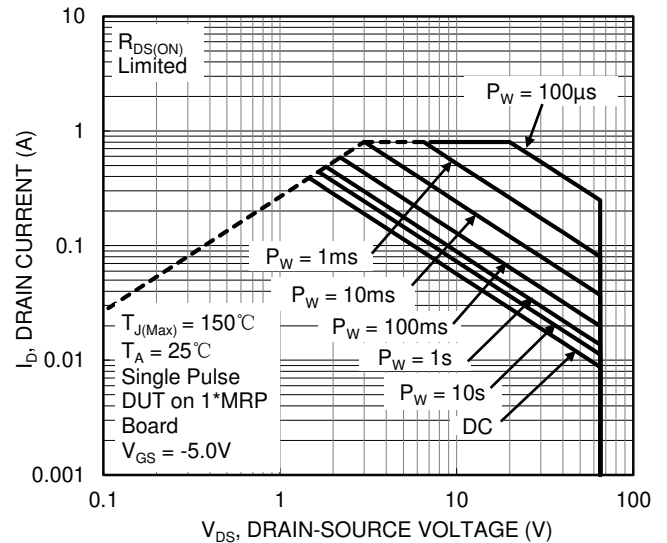


Figure 12. SOA, Safe Operation Area

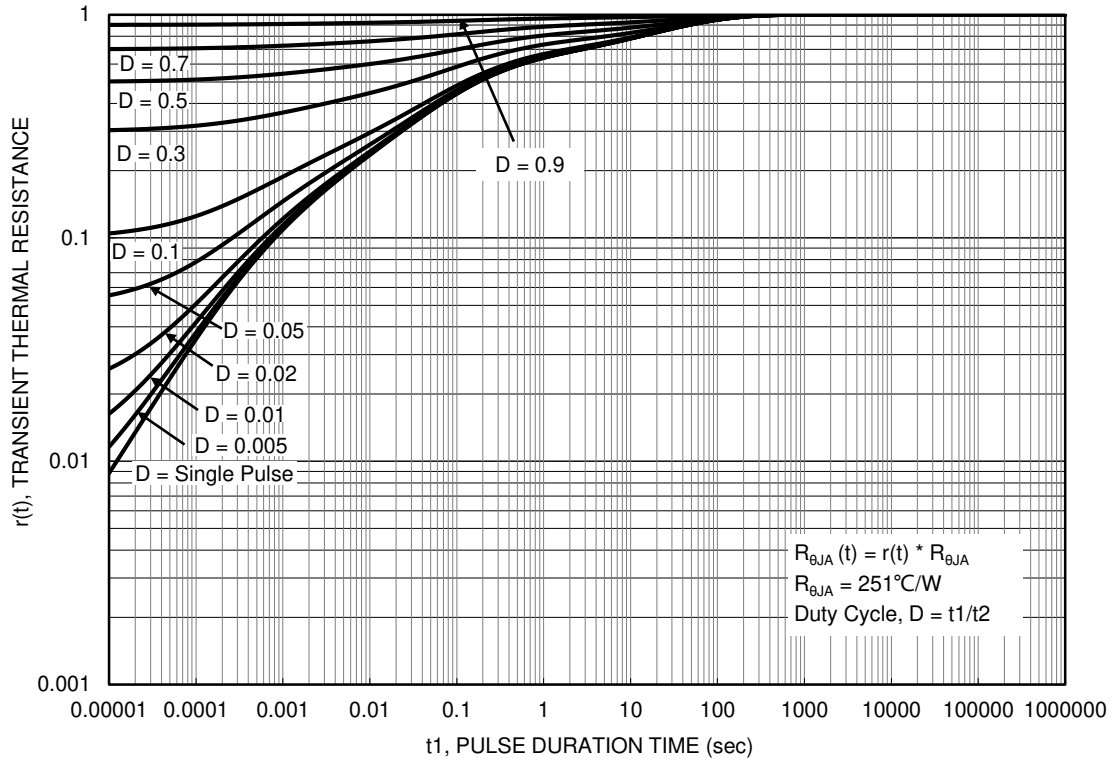
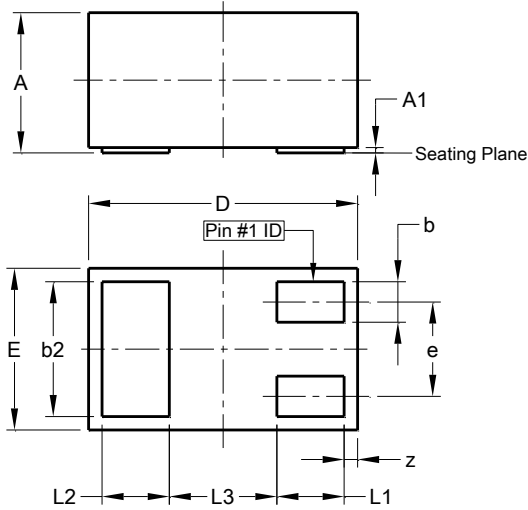


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

X1-DFN1006-3

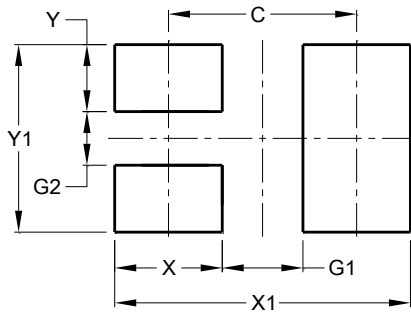


X1-DFN1006-3			
Dim	Min	Max	Typ
A	0.47	0.53	0.50
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.075	1.00
E	0.55	0.675	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70

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